Ordering number : ENA1204A

DBD250G

25.0A Single-Phase Bridge Rectifier

ON Semiconductor®

http://onsemi.com

Features

- Plastic molded structure
- Glass passivation for high reliability
- Peak reverse voltage : V_{RM}=600V
- Average output current : I_O=25.0A

Specifications

Absolute Maximum Ratings at Tc=25°C

Parameter	Symbol	Conditions	Raitings	Unit
Peak Reverse Voltage	V_{RM}		600	V
Average Output Current	I_O	Ta=40°C	6.0	A
		Ta=40°C, With 300×300×3.0mm^3 Cu fin	25.0	A
Surge Forward Current	I_{FSM}	50Hz sine wave, 1cycle	400	A
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		−40 to +150	°C
Dilective Strength Voltage	VIS	Terminals tc case, AC 1 minute	2	kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics at Tc=25°C *Per Constituent element of bridge.

Parameter	Symbol	Conditions	Raitings			Unit
			min	typ	max	
Forward Voltage	V_F	I_F=12.5A*			1.05	V
Reverse Current	I_R	V_R:At each V_{RM}*			10	μA
Thremal Resistance	Rth(j-c)	Junction-Case			1.5	°C / W

Note) Maximum tightening torque : 0.98Nm

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Package Dimensions

unit:mm(typ.)